L Number	Hits	1	TDB	Time stamp
	2102	(tab near3 lead) and semiconductor and (chip die wafer)	USPAT; US-PGPUB;	2003/05/19 08:33
2	1640	(/tab poor2 look) and marine	EPO; JPO; DERWENT	
i	1040	((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with	USPAT; US-PGPUB;	2003/05/19 08:36
		(electrode bump ball terminal pad))	EPO; JPO; DERWENT	
3	123	(((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with	USPAT; US-PGPUB;	2003/05/19 08:37
		(clectrode bump ball terminal pad))) and (conductive nearl (vias (through adj hole)))	EPO; JPO; DERWENT	
4	94	((((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with (clectrode bump ball terminal pad))) and	USPAT; US-PGPUB; EPO; JPO;	2003/05/19 08:38
		<pre>(conductive near1 (vias (through adj hole)))) and (seal sealed scaling</pre>	DERWENT	
5	43	encapsulant encapsulated encapsulating) (((((tab near3 lead) and semiconductor and (chip die wafer)) and (lead with (electrode bump ball terminal pad))) and (conductive near1 (vias (through adj	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/05/19 08:38
		hole)))) and (seal scaled scaling encapsulant encapsulated encapsulating))	DEKMENI	
I		and (stacked stacking)		